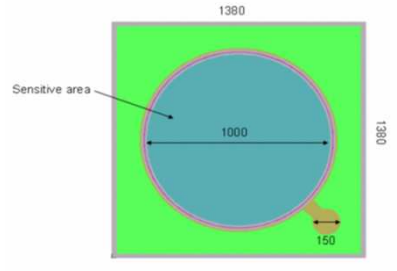


Data Sheet

PIN Photodiode Chip IR

EOPC-1300-1.0

Radiation	Type	Electrodes
infrared	InGaAs	p (anode) up

	<p>Description:</p> <p>Broadband photodiode with maximum response in the NIR-region (800-1750 nm)</p> <p>Sensitive area is typical 1000 μm in diameter, chip thickness 200±30 μm</p> <p>Features:</p> <ul style="list-style-type: none"> optical power monitor PD low dark current and low capacitance
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ELECTRO-OPTICAL CHARACTERISTICS:

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Responsivity	R	0.8	0.95		A/W	$V_R=5V, \lambda=1310nm @ 25C$
Dark Current	I_D		2	20	nA	$V_R=5V @ 25C$
Breakdown Voltage	V_{BD}	20	35		V	$I_R=10\mu A$
Capacitance	C		100	200	pF	$V_R=0V, f=1 MHz$

ABSOLUTE MAXIMUM RATINGS:

PARAMETERS	MIN	MAX	UNIT	CONDITIONS
Storage temperature	-40	100	°C	
Operating temperature	-40	85	°C	
Reverse current		2	mA	
Forward current		10	mA	
Reverse voltage		20	V	

TYPICAL EO PERFORMANCE :

Fig. 1 Typical Dark Current and Forward Current

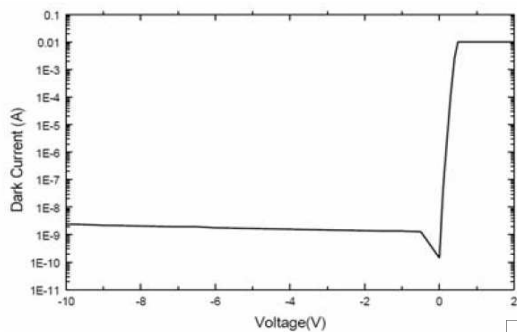
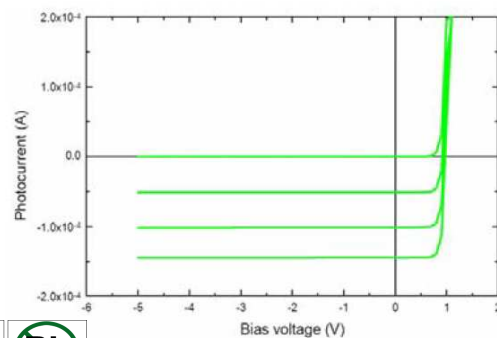


Fig. 2 Typical Photo-Current



Data Sheet

PIN Photodiode Chip IR

EOPC-1300-1.0

Radiation	Type	Electrodes
infrared	InGaAs	p (anode) up

Fig. 3 Typical Breakdown Curve

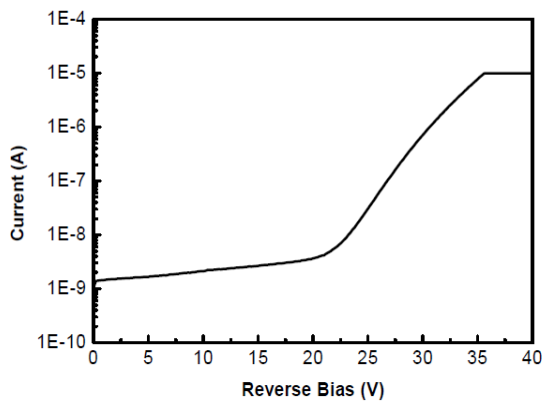


Fig. 4 Typical C-V Curve

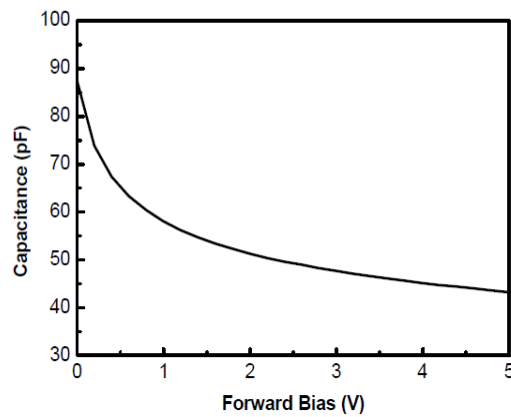
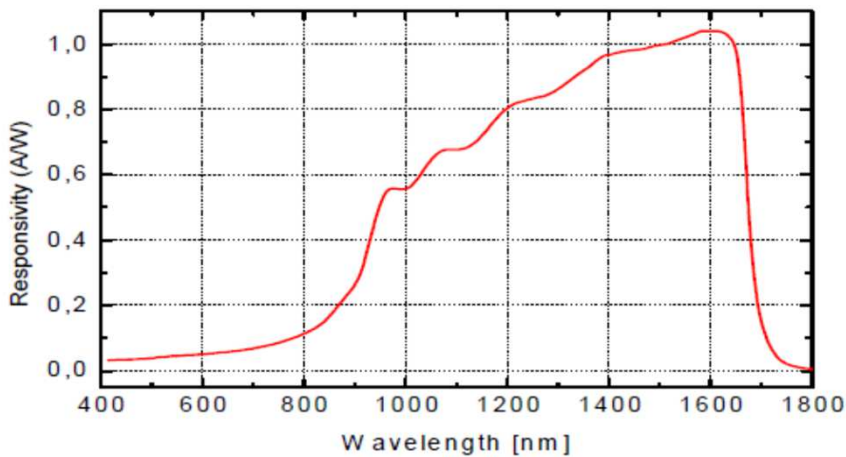


Fig. 5 Typical Optical Responsivity



Art. No. 123 001



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.